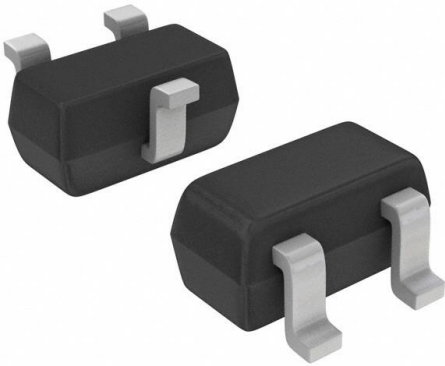


NSVMMBT3906TT1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NSVMMBT3906TT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NSVMMBT3906TT1G
Description	TRANS PNP 40V 0.2A SC75 SOT416
Detailed Description	Bipolar (BJT) Transistor PNP 40 V 200 mA 250MHz 200 mW Surface Mount SC-75, SOT-416



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NSVMMBT3906TT1G

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

40 V

Current - Collector Cutoff (Max):

-

Power - Max:

200 mW

Operating Temperature:

-55°C ~ 150°C (TJ)

Qualification:

AEC-Q101

Package / Case:

SC-75, SOT-416

Base Product Number:

NSVMMBT3906

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

200 mA

Vce Saturation (Max) @ Ib, Ic:

400mV @ 5mA, 50mA

DC Current Gain (hFE) (Min) @ Ic, Vce:

100 @ 10mA, 1V

Frequency - Transition:

250MHz

Grade:

Automotive

Mounting Type:

Surface Mount

Supplier Device Package:

SC-75, SOT-416

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

General Purpose Transistors

PNP Silicon

MMBT3906TT1

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-416/SC-75 package which is designed for low power surface mount applications.

Features

- NSVM Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-40	Vdc
Collector-Base Voltage	V_{CBO}	-40	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-200	mAdc

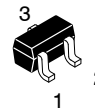
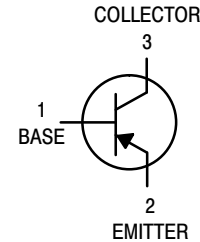
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derated above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
Total Device Dissipation, FR-4 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derated above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

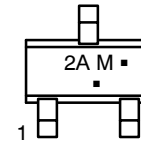
1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0×1.0 Inch Pad

GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



CASE 463
SOT-416/SC-75
STYLE 1

MARKING DIAGRAM



2A = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906TT1G	SOT-416 (Pb-Free)	3000 / Tape & Reel
NSVMMBT3906TT1G	SOT-416 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT3906TT1**ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) ($I_C = -1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = -10\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	-40	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Base Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB} = -3.0\text{ Vdc}$)	I_{BL}	-	-50	nAdc
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB} = -3.0\text{ Vdc}$)	I_{CEX}	-	-50	nAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -10\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -50\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	60 80 100 60 30	- - 300 - -	-
Collector – Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -1.0\text{ mAdc}$) ($I_C = -50\text{ mAdc}$, $I_B = -5.0\text{ mAdc}$)	$V_{CE(sat)}$	- -	-0.25 -0.4	Vdc
Base – Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -1.0\text{ mAdc}$) ($I_C = -50\text{ mAdc}$, $I_B = -5.0\text{ mAdc}$)	$V_{BE(sat)}$	-0.65 -	-0.85 -0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ($I_C = -10\text{ mAdc}$, $V_{CE} = -20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	250	-	MHz
Output Capacitance ($V_{CB} = -5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	-	4.5	pF
Input Capacitance ¹ ($V_{EB} = -0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	-	10.0	pF
Input Impedance ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	2.0	12	k Ω
Voltage Feedback Ratio ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{re}	0.1	10	$\times 10^{-4}$
Small – Signal Current Gain ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	100	400	-
Output Admittance ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	3.0	60	μmhos
Noise Figure ($V_{CE} = -5.0\text{ Vdc}$, $I_C = -100\ \mu\text{Adc}$, $R_S = 1.0\text{ k}\ \Omega$, $f = 1.0\text{ kHz}$)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	($V_{CC} = -3.0\text{ Vdc}$, $V_{BE} = 0.5\text{ Vdc}$)	t_d	-	35	ns
Rise Time	($I_C = -10\text{ mAdc}$, $I_{B1} = -1.0\text{ mAdc}$)	t_r	-	35	
Storage Time	($V_{CC} = -3.0\text{ Vdc}$, $I_C = -10\text{ mAdc}$)	t_s	-	225	ns
Fall Time	($I_{B1} = I_{B2} = -1.0\text{ mAdc}$)	t_f	-	75	

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MMBT3906TT1

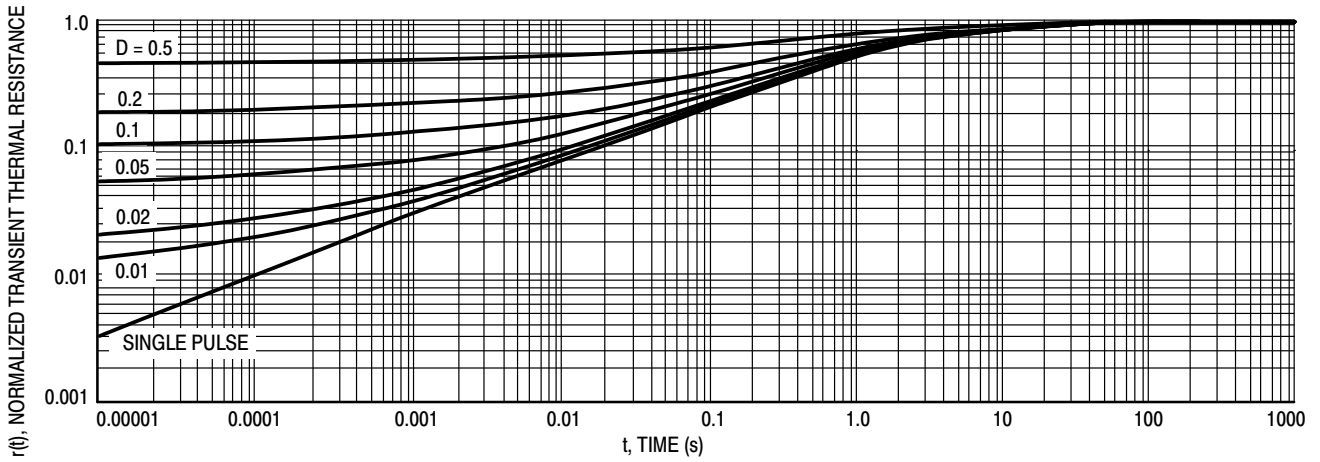


Figure 1. Normalized Thermal Response

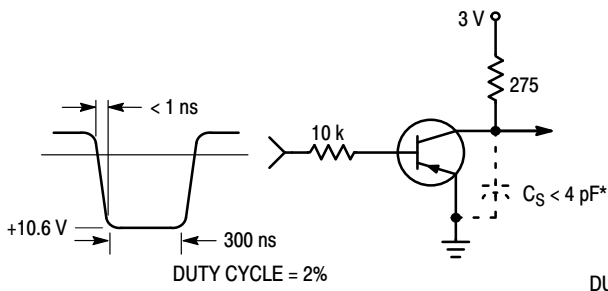


Figure 2. Delay and Rise Time Equivalent Test Circuit

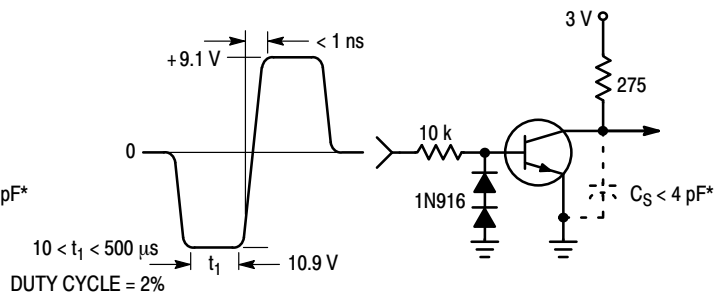


Figure 3. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

MMBT3906TT1

TYPICAL TRANSIENT CHARACTERISTICS

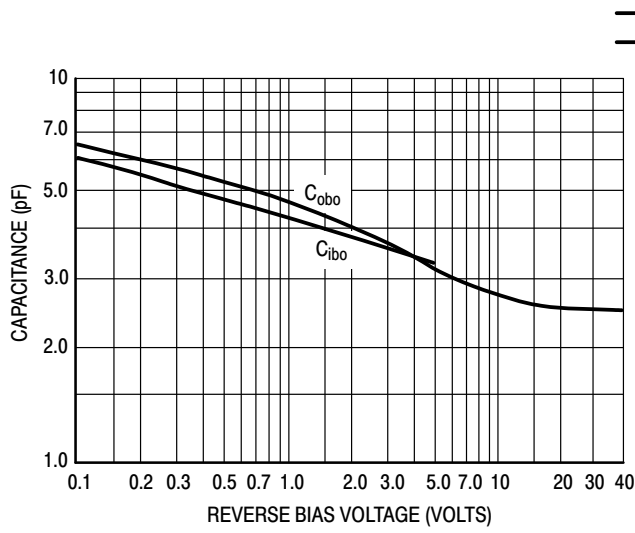


Figure 4. Capacitance

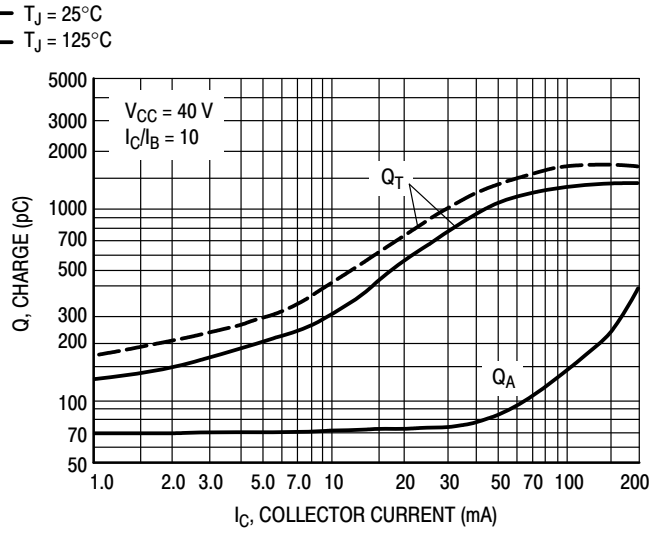


Figure 5. Charge Data

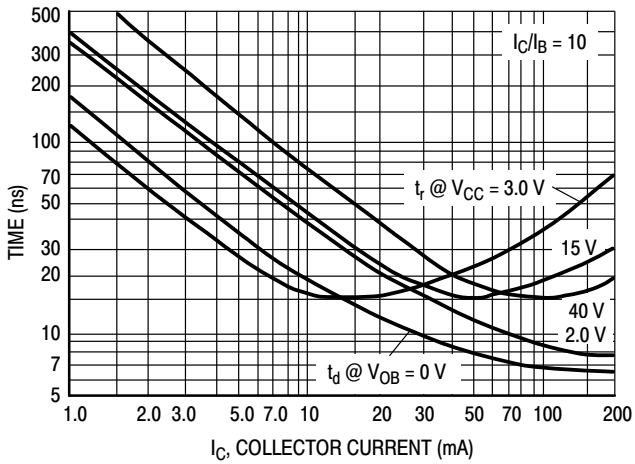


Figure 6. Turn-On Time

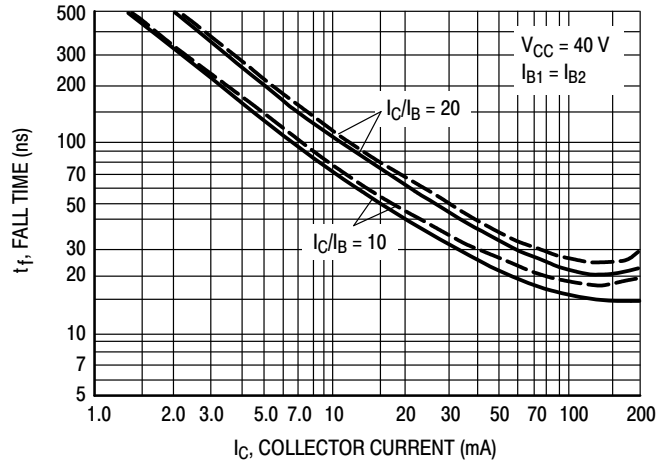


Figure 7. Fall Time

MMBT3906TT1

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

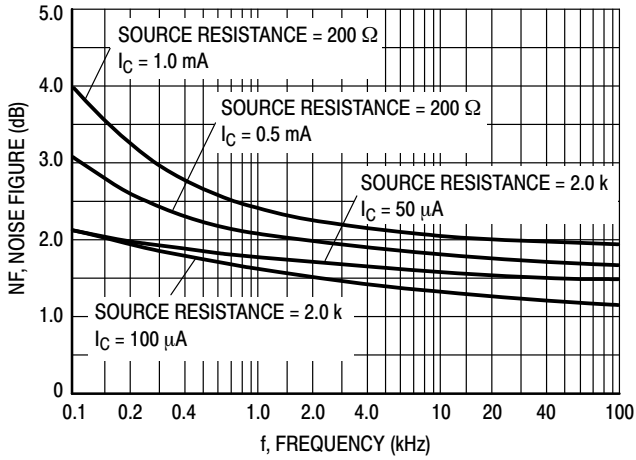


Figure 8.

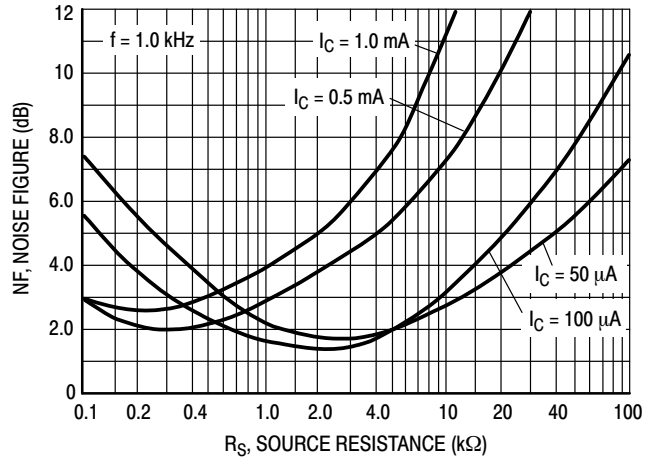


Figure 9.

h PARAMETERS

($V_{CE} = -10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

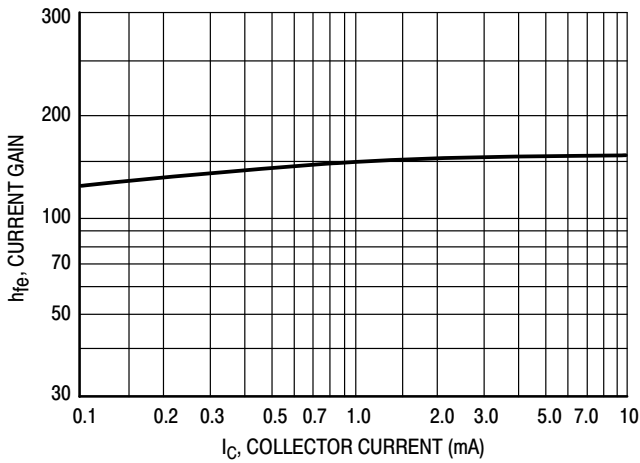


Figure 10. Current Gain

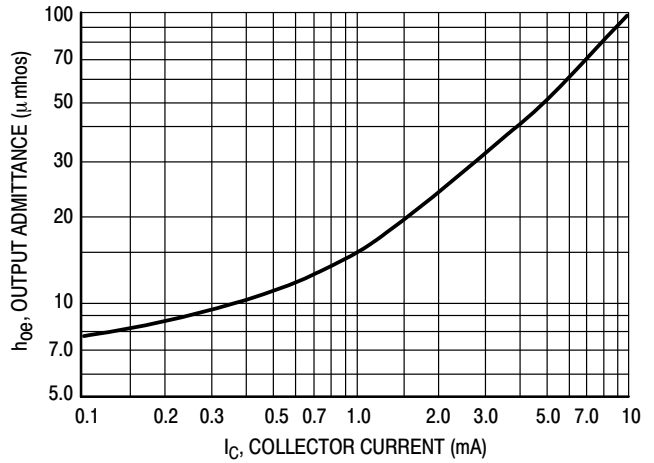


Figure 11. Output Admittance

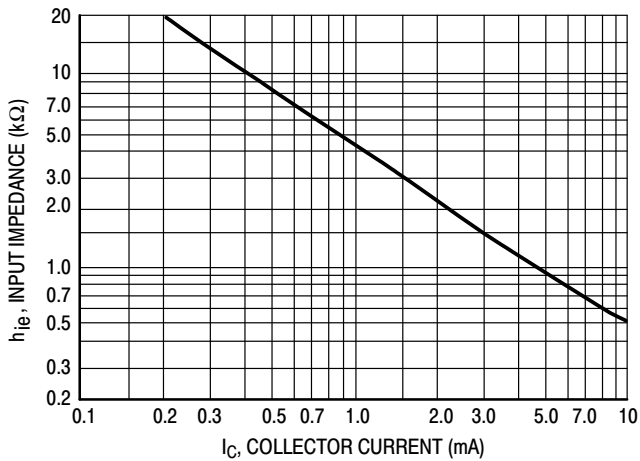


Figure 12. Input Impedance

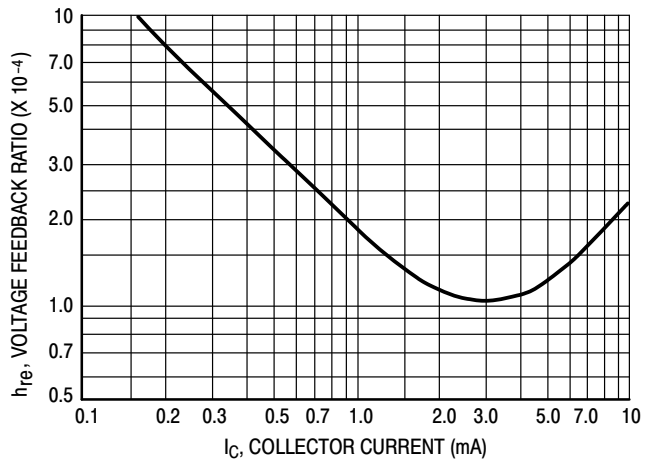


Figure 13. Voltage Feedback Ratio

MMBT3906TT1

STATIC CHARACTERISTICS

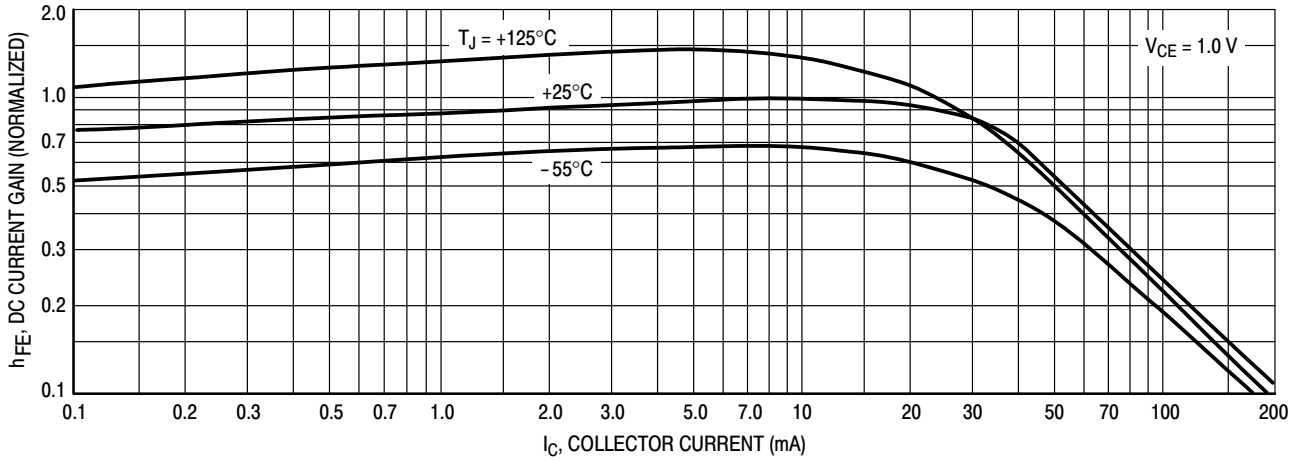


Figure 14. DC Current Gain

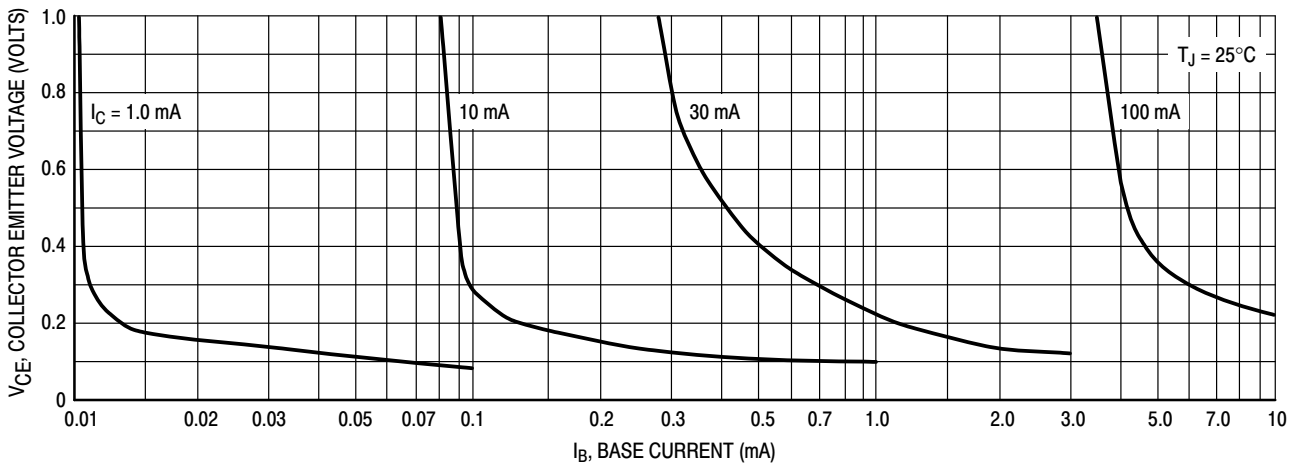


Figure 15. Collector Saturation Region

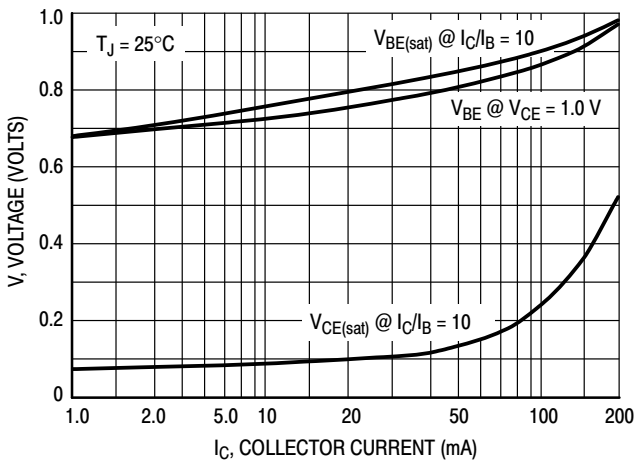


Figure 16. "ON" Voltages

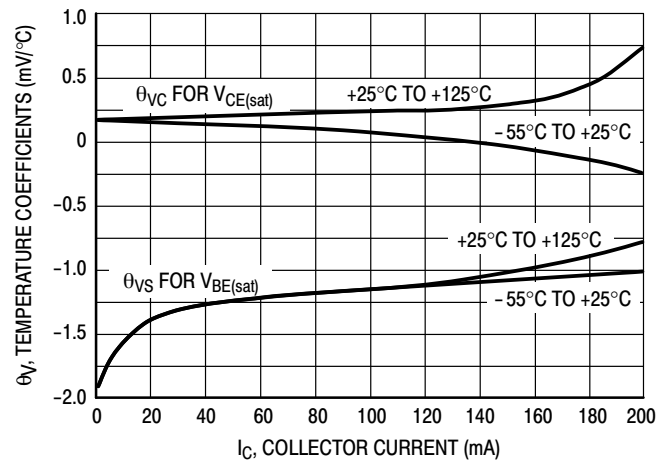


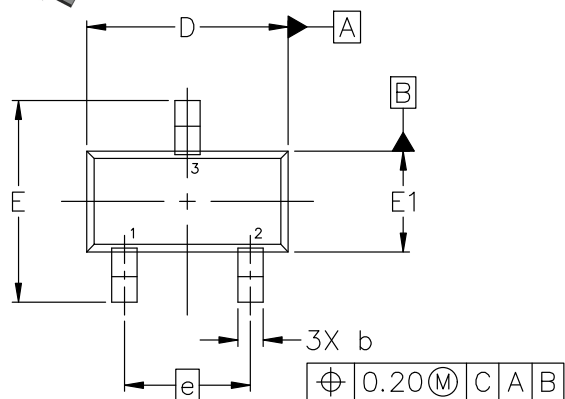
Figure 17. Temperature Coefficients



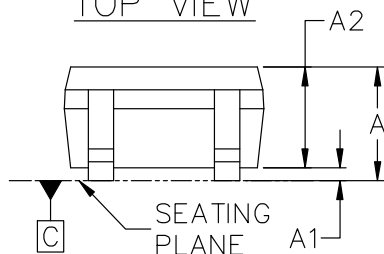
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

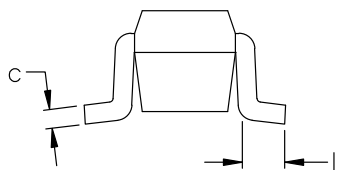
DATE 01 FEB 2024



TOP VIEW



SIDE VIEW



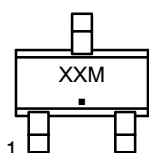
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20

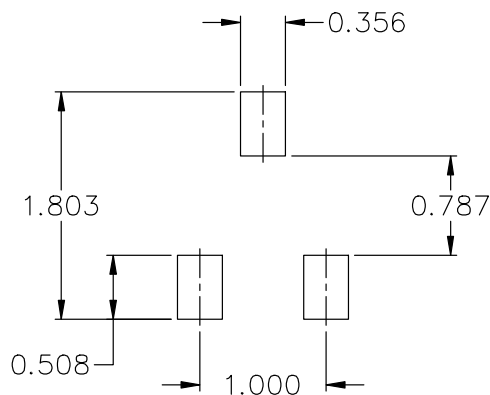
GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we strictly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.